



GK35FF60A1H-C

IGBT Module

Preliminary Data

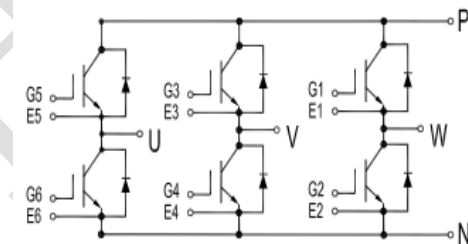
Features:

- Non Punch Through (NPT) Technology
- Short Circuit Rated >10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2xIc)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Inverters
- Servo Applications
- UPS Systems



IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ\text{C}$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		600	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ\text{C}$,	35	A
		$T_C = 25^\circ\text{C}$	60	A
I_{CM}	Repetitive Peak Collector Current	$T_J = 150^\circ\text{C}$	70	A
t_{sc}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	$T_C = 25^\circ\text{C}$ $T_{Jmax}=150^\circ\text{C}$	220	W



Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	3.0	4.5	5.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 35 \text{ A}, V_{GE} = 15 \text{ V}$	$T_J = 25^\circ\text{C}$	1.80	2.00	V
			$T_J = 125^\circ\text{C}$	2.00		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}, T_J = 25^\circ\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		1.75		nF
C_{oes}	Output Capacitance			0.16		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 300 \text{ V}, I_C = 35 \text{ A}, R_G = 20 \Omega, V_{GE} = \pm 15 \text{ V},$ Inductive Load	$T_J = 25^\circ\text{C}$	70		ns
			$T_J = 125^\circ\text{C}$	60		
t_r	Rise Time		$T_J = 25^\circ\text{C}$	50		ns
			$T_J = 125^\circ\text{C}$	55		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$	130		ns
			$T_J = 125^\circ\text{C}$	135		
t_f	Fall Time		$T_J = 25^\circ\text{C}$	90		ns
			$T_J = 125^\circ\text{C}$	110		
E_{on}	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$	0.29		mJ
			$T_J = 125^\circ\text{C}$	0.42		
E_{off}	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$	0.31		mJ	
		$T_J = 125^\circ\text{C}$	0.50			
Q_g	Total Gate Charge	$T_J = 25^\circ\text{C}$	80		nC	
RBSOA	Reverse Bias Safe Operation Area	$I_C=70\text{A}, V_{CC}=480\text{V}, V_p=600\text{V}, R_g = 15\Omega, V_{GE}=\pm 15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid			
SCSOA	Short Circuit Safe Operation Area	$V_{CC} = 300 \text{ V}, V_{GE} = 15 \text{ V}, T_J = 150^\circ\text{C}$	5			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case			0.57		$^\circ\text{C/W}$



Diode, Inverter

Maximum Rated Values ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	600	V
I_F	Diode Continuous Forward Current	35	A
I_{FM}	Diode Maximum Forward Current	70	A

Electrical Characteristics of FWD ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{FM}	Forward Voltage	$I_F = 35\text{ A}$	$T_J = 25^{\circ}\text{C}$	1.50	1.70	V
			$T_J = 125^{\circ}\text{C}$	1.50		
I_{rr}	Peak Reverse Recovery Current		$T_J = 25^{\circ}\text{C}$	30		A
			$T_J = 125^{\circ}\text{C}$	35		
Q_{rr}	Reverse Recovery Charge	$I_F = 35\text{ A}$, $di/dt = 960\text{ A}/\mu\text{s}$, $V_{rr} = 300\text{ V}$, $V_{GE} = -15\text{ V}$	$T_J = 25^{\circ}\text{C}$	1.51		μC
			$T_J = 125^{\circ}\text{C}$	2.43		
E_{rec}	Reverse Recovery Energy		$T_J = 25^{\circ}\text{C}$	0.14		mJ
			$T_J = 125^{\circ}\text{C}$	0.34		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case			1.51		$^{\circ}\text{C}/\text{W}$

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage (All Terminals Shorted)	$f = 50\text{ Hz}$, 1minute	2500			V
T_J	Maximum Junction Temperature				150	$^{\circ}\text{C}$
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40		+125	$^{\circ}\text{C}$
CTI	Comparative Tracking Index		200			
$R_{\theta CS}$	Case-To-Sink Thermally (Conductive Grease Applied)			0.1		$^{\circ}\text{C}/\text{W}$
T	Mounting Screw:M3		1.5		2.0	N·m
G	Weight			30		g

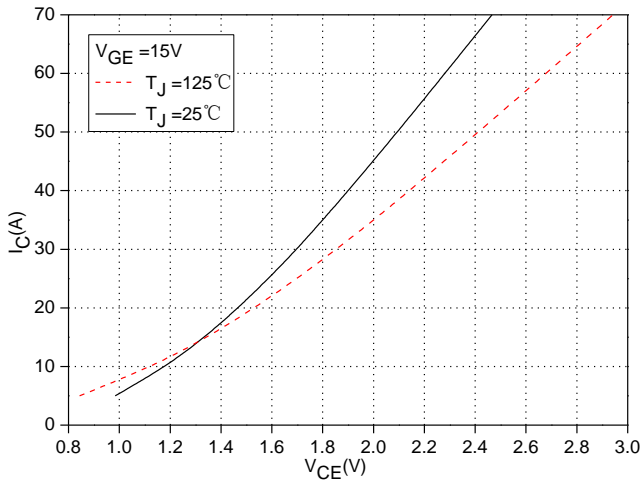


Fig.1 Typical Saturation Voltage Characteristics

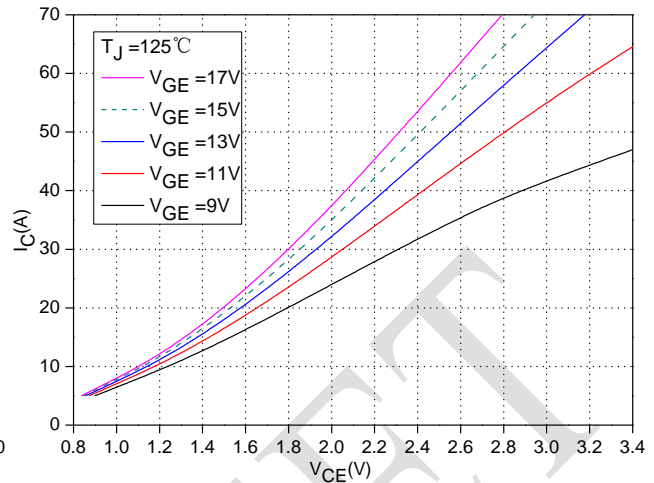


Fig.2 Typical Output Characteristics

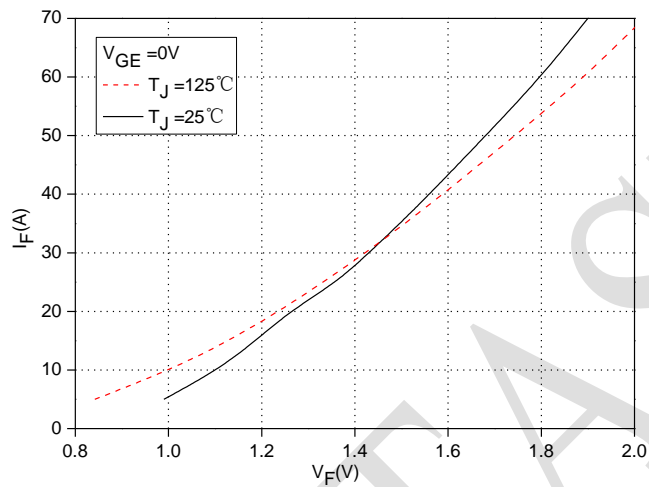


Fig.3 Forward Characteristics of FWD

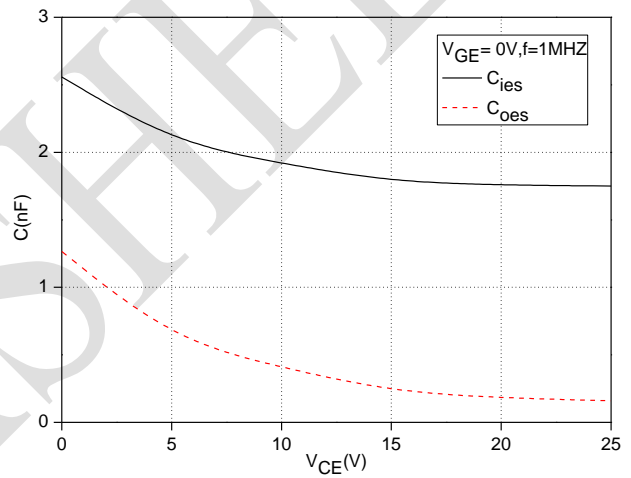


Fig.4 Capacitance Characteristics

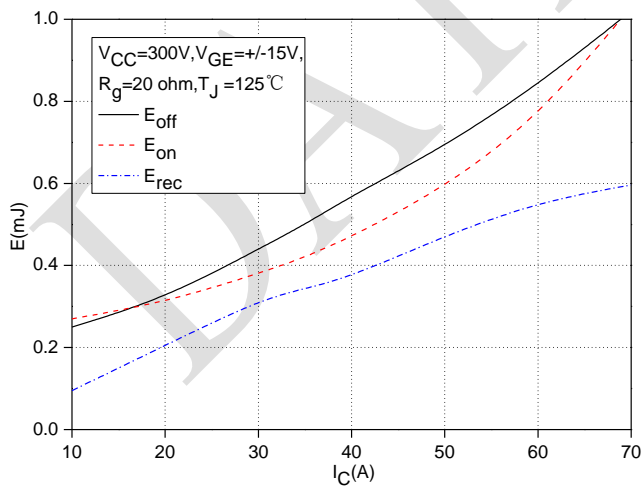


Fig.5 Typical Switching Losses vs. Collector Current

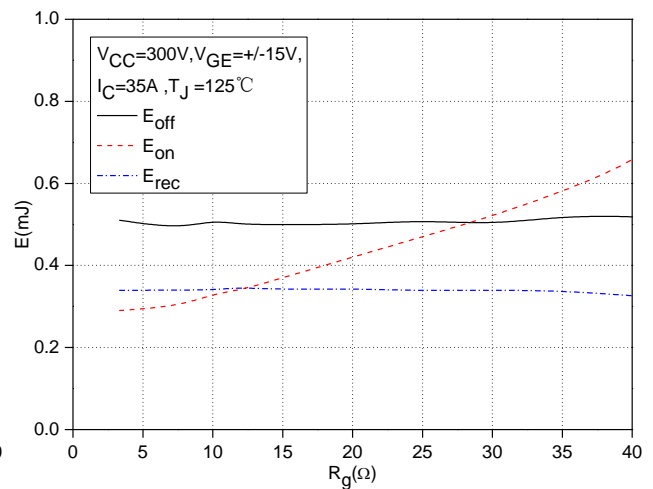


Fig.6 Typical Switching Loss vs. Gate Resistance

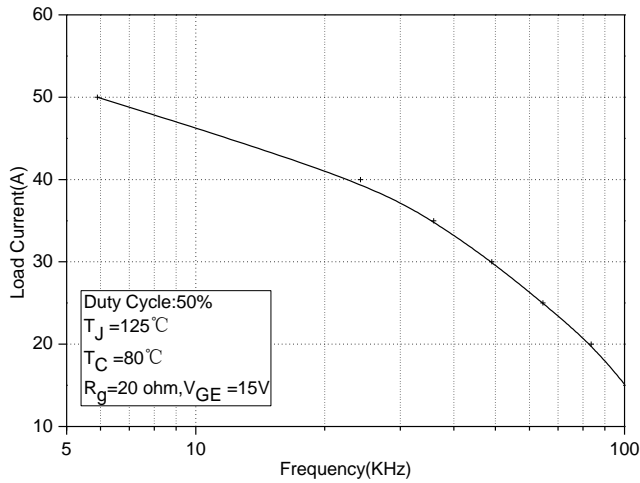


Fig.7 Typical Load Current vs. Frequency

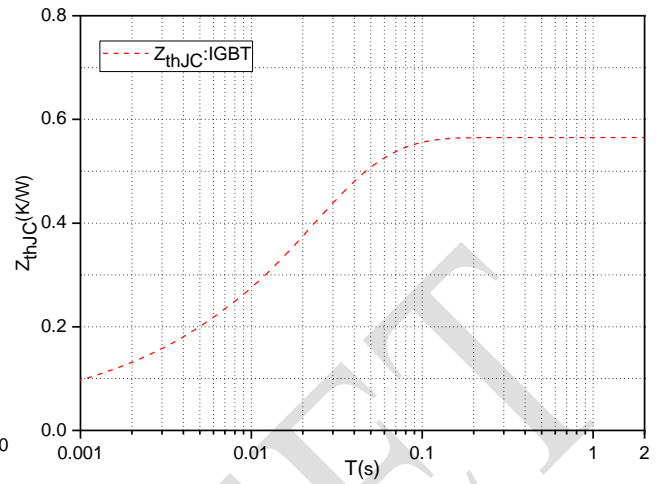


Fig.8 Transient Thermal Impedance (IGBT)

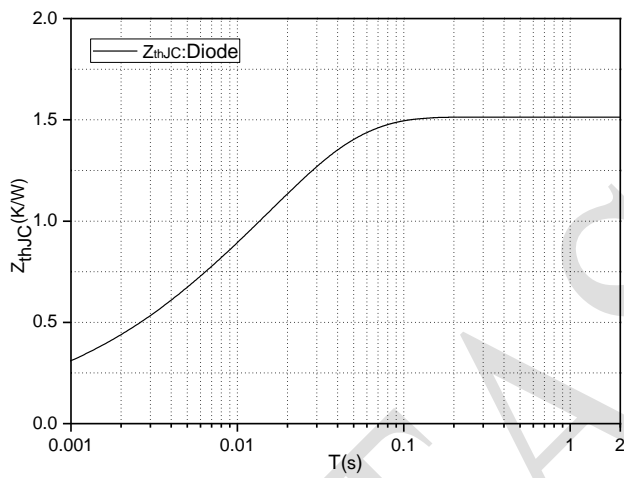


Fig.9 Transient Thermal Impedance (Diode)

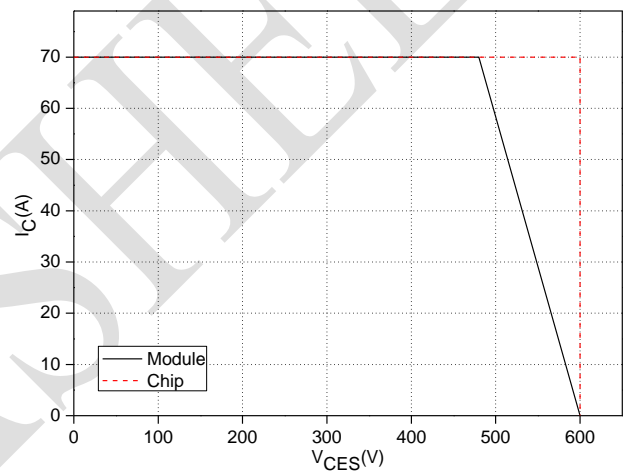
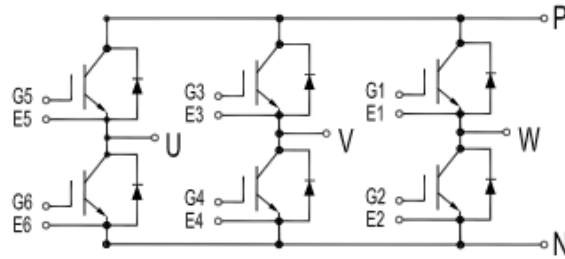


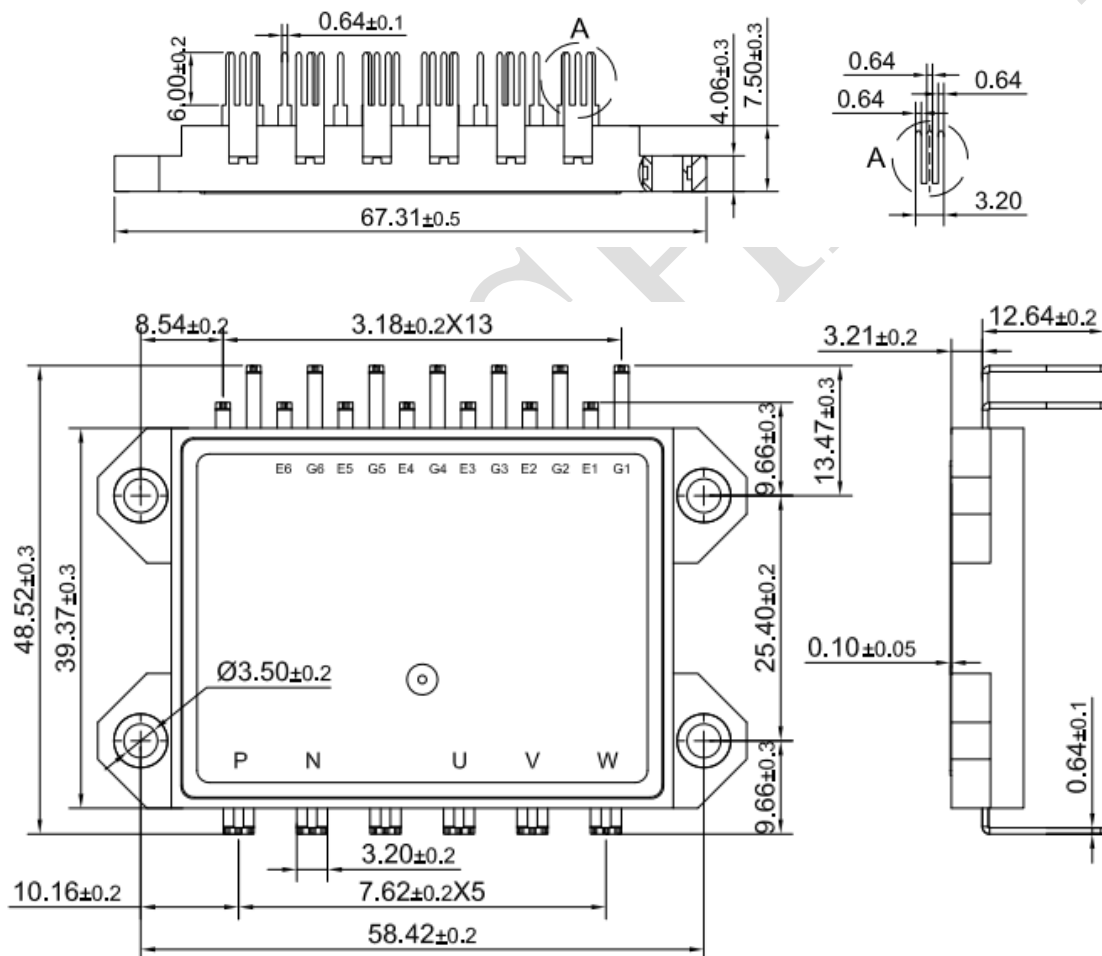
Fig.10 Reverse Bias Safe Operation Area (RBSOA)



Internal Circuit:



Package Outline (Unit: mm):





Date	Revision	Notes
12/20/2019	01	Initial Release

Announcement

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